

FAST RECOVERY RECTIFIER DIODES

FEATURES

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING
- SURFACE MOUNT DEVICE



DESCRIPTION

Single high voltage rectifier ranging from 200V to 400 V suited for Switch Mode Power Supplies and other power converters.

SOD6
(Plastic)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$I_F(\text{RMS})$	RMS forward current	10	A
$I_F(\text{AV})$	Average forward current	1	A
$I_{F\text{SM}}$	Non repetitive surge peak forward current	30	A
$T_{\text{stg}}\ T_j$	Storage and junction temperature range	- 40 to + 150 - 40 to + 150	°C °C

Symbol	Parameter	SMBYT01-			Unit
		200	300	400	
V_{RRM}	Repetitive peak reverse voltage	200	300	400	V

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{\text{th}}(j-l)$	Junction-leads	25	°C/W

ELECTRICAL CHARACTERISTICS**STATIC CHARACTERISTICS**

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V _F *	T _j = 25°C	I _F = 1 A			1.5	V
	T _j = 100°C				1.4	
I _R **	T _j = 25°C	V _R = V _{RRM}			20	μA
	T _j = 100°C				0.5	

Pulse test : * tp = 380 μs, duty cycle < 2 %

** tp = 5 ms, duty cycle < 2 %

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
trr	T _j = 25°C	I _F = 0.5A	I _{rr} = 0.25A		25	ns
		I _R = 1A			60	
		I _F = 1A	dI _F /dt = -15A/μs			
		V _R = 30V				

TURN-OFF SWITCHING CHARACTERISTICS (Without serie inductance)

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
t _{IRM}	V _{CC} = 200V	I _F = 1A	L _p ≤ 0.05μH		35	50	ns
I _{RM}	T _j = 100°C	dI _F /dt = -50A/μs			1.5	2	A

To evaluate the conduction losses use the following equation :

$$P = 1.1 \times I_{F(AV)} + 0.25 \times I_{F(RMS)}^2$$

Voltage (V)	200	300	400
Marking	B2	B3	B4

Laser marking

Logo indicates cathode

Fig.1 : Low frequency power losses versus average current.

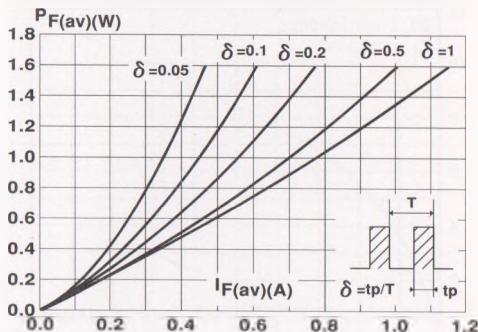


Fig.3 : Non repetitive surge peak forward current versus overload duration.

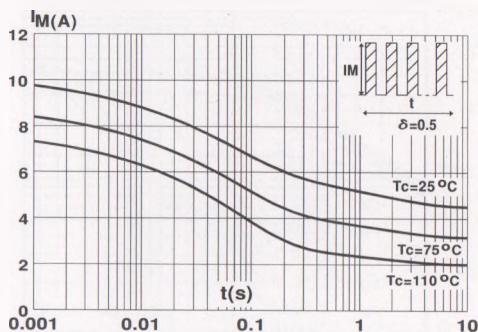


Fig.5 : Voltage drop versus forward current. (Maximum values)

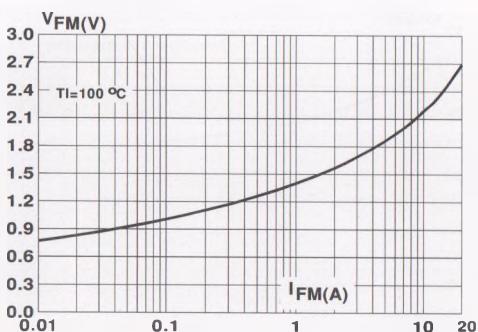


Fig.2 : Peak current versus form factor.

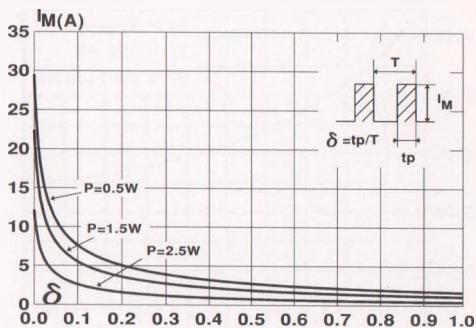


Fig.4 : Relative variation of thermal impedance junction to lead versus pulse duration.

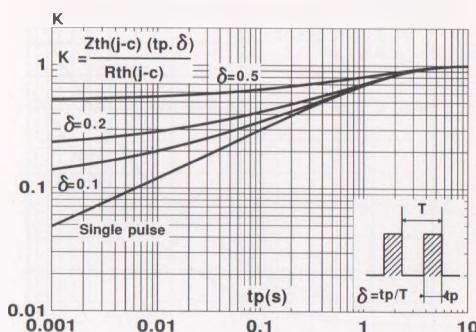


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)

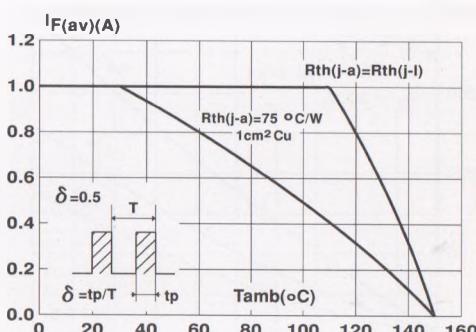


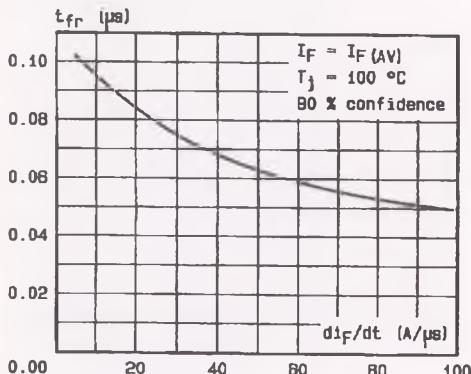
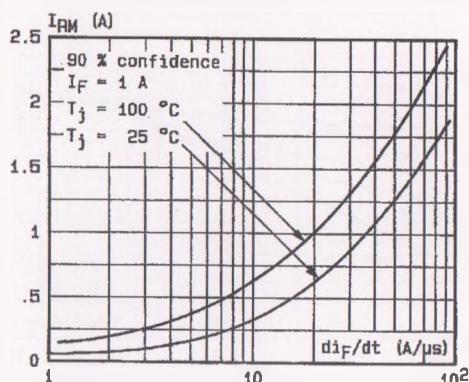
Fig.7 : Recovery time versus dI_F/dt .Fig.9 : Peak reverse current versus dI_F/dt .

Fig.11 : Dynamic parameters versus junction temperature.

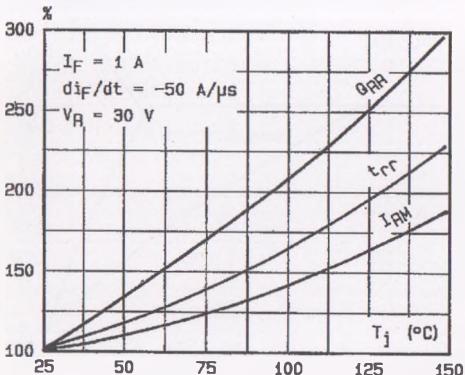
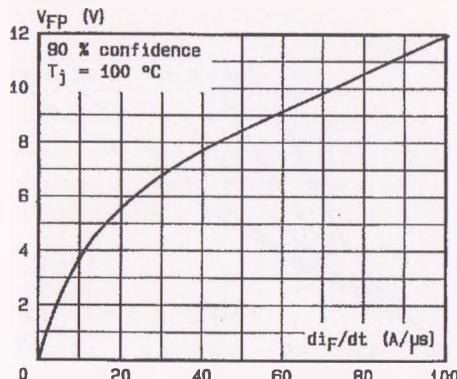
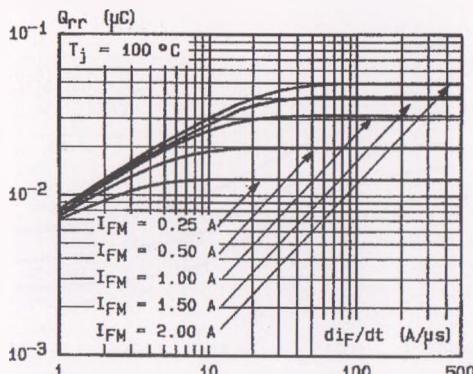
Fig.8 : Peak forward voltage versus dI_F/dt .Fig.10 : Recovery charge versus dI_F/dt . (typical values)

Fig.12 : Thermal resistance junction to ambient versus copper surface under each lead.

